Silicon Carbide Diode

Rev.01 - 21 June 2022

Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.



- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T_{i(max)} = 175 °C)

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				1200		V
I _{O(AV)}	limiting average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 148 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		10			А
T _j	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$		-	1.42	1.60	V
		I _F = 5 A; T _j = 150 °C; per diode; <u>Fig. 5</u>		-	1.90	2.30	V
		$I_{F} = 5 \text{ A}; T_{j} = 175 \text{ °C}; \text{ per diode}; Fig. 5$		-	2.00	2.50	V
Dynamic	characteristics		,			,	
Q _r	recovered charge	$I_F = 5 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	11	-	nC
,							



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5. Pinning information

Table 2. I	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	К	cathode		
3	A2	anode		К К
mb	mb	mounting base; connected to cathode		sym125

6. Ordering information

Table 3. Ordering information										
Type number	Package	Orderable part number	Packing	Small packing	Package	Package				
	name		method	quantity	version	issue date				
WNSC2D101200CW	TO247	WNSC2D101200CW6Q	Tube	30	SOT429	25-Mar-2013				

7. Marking

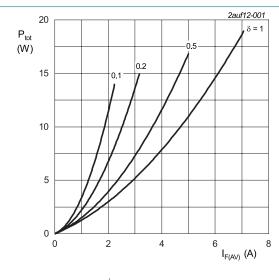
Table 4. Marking codes									
Type number	Marking codes								
WNSC2D101200CW	WNSC2D 101200CW								

8. Limiting values

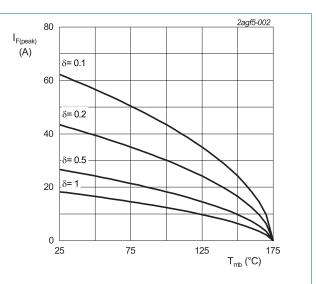
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			1200	V
V_{RWM}	crest working reverse voltage			1200	V
V _R	reverse voltage	DC		1200	V
I _{O(AV)}	limiting average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 148 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 149 °C; square-wave pulse; per diode		10	A
I _{FSM}	non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		45	A
		t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode		450	A
l ² t	l ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms		10.13	A ² s
T _{stg}	storage temperature			-55 to 175	°C
Tj	junction temperature			-55 to 175	°C



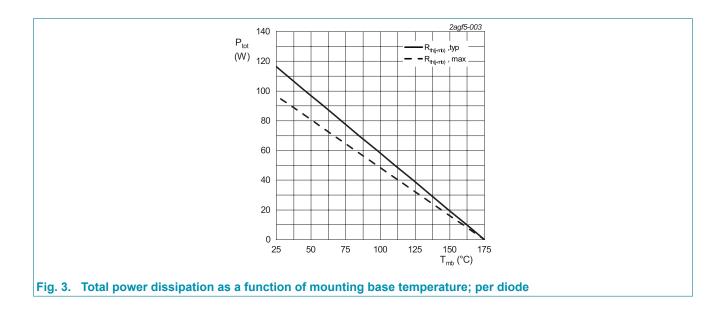
 $\begin{array}{l} {\sf I}_{\sf F(AV)} = {\sf I}_{\sf F(RMS)} \times \sqrt{\delta} \\ {\sf V}_{\sf o} = 1.027 \; V; \; {\sf R}_{\sf s} = 0.2336 \; \Omega \end{array}$ Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode





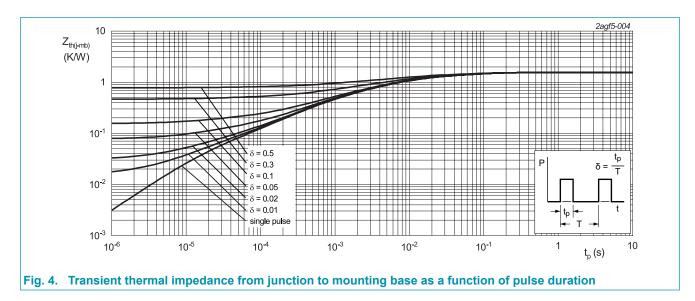
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WNSC2D101200CW Silicon Carbide Diode



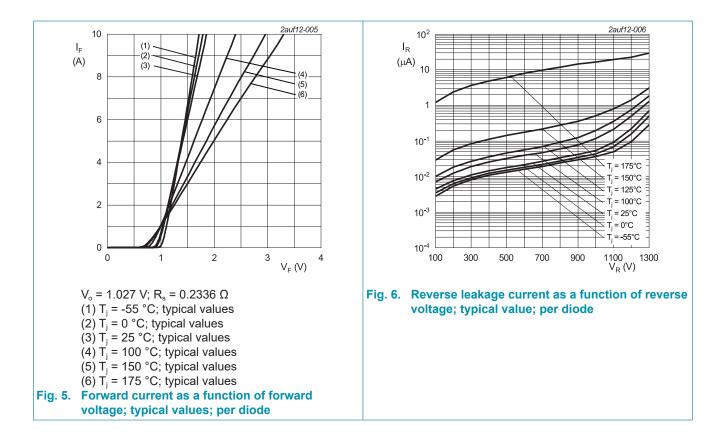
9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to mounting base	per diode; <u>Fig. 4</u>		-	1.29	1.55	K/W	
	-	both diodes conducting		-	0.65	0.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



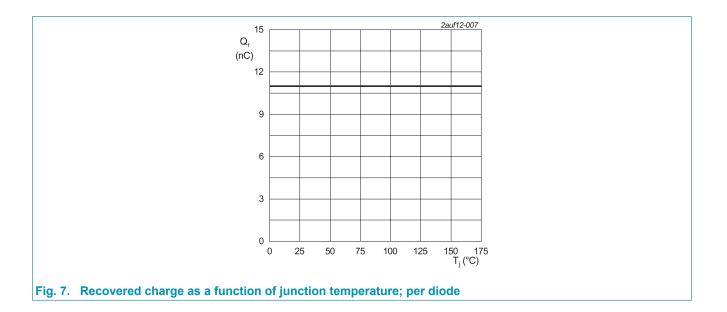
10. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V _F	forward current	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$		-	1.42	1.60	V
		$I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; \text{Fig. 5}$		-	1.90	2.30	V
		$I_{F} = 5 \text{ A}; T_{j} = 175 \text{ °C}; \text{ per diode}; Fig. 5$		-	2.00	2.50	V
I _R reverse current		V_{R} = 1200 V; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.5	25	μA
		V _R = 1200 V; T _j = 175 °C; per diode; <u>Fig. 6</u>		-	25	300	μA
Dynamic	characteristics	·					
Q _r	recovered charge	$I_F = 5 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	11	-	nC
C _d	diode capacitance	f = 1 MHz; V_R = 1 V; T_j = 25 °C; per diode		-	260	-	pF
		f = 1 MHz; V_R = 400 V; T_j = 25 °C; per diode		-	22	-	pF
		f = 1 MHz; V_R = 800 V; T_j = 25 °C; per diode		-	16	-	pF
E _{as}	non-repetitive avalanche energy	I_R = 2.9 A; L = 10 mH; $T_{j(init)}$ = 25 °C; per diode		42	-	-	mJ



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11. Package outline

lastic single-end	ed thr	rough	1-hole	pack	age;	heats	ink m	ounte	ed; 1 i	mount	ting h	ole; 3	lead	ТО-2	247					SOT429
						52- 2 3	0	-				20	mm							
Dimensions (mm ar	e the c	original	l dimen	isions)					SCa	ale										
Unit ⁽¹⁾ A	A ₁	b	b ₁	b ₂	с	D	D ₁	D ₂	Е	E ₁	E ₂	E ₃	e ⁽¹⁾	L	L ₁	P ₂	р	Q	q	ø
max 5.20 mm nom	2.10	1.40	2.20	3.20	0.70	20.6	17.68	1.20	15.75	14.22	5.20	1.80	5.45	20.90	4.75	3.60	3.70	2.60	6.18	7.30
min 4.70	1.90	1.00	1.80	2.80	0.50	20.3	17.28	0.80	15.45	13.82	4.80	1.40		20.40	4.25	3.40	3.50	2.20	5.78	7.10
Note	etween	center	rs.																so	t429_po
						R	eferenc	ces							Europ	bean				
1. Basic spacing be			IEC JEDEC JEITA							projection				Issue date						
		IEC	>		JED	EC		JE	EITA						proje	ction			sue da 4-09-1	

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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